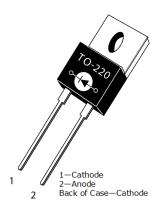


MSC030SDA120K Zero Recovery Silicon Carbide Schottky Diode

1 Product Overview

The silicon carbide (SiC) power Schottky barrier diodes (SBD) product line from Microsemi increases your performance over silicon diode solutions while lowering your total cost of ownership for high-voltage applications. The MSC030SDA120K is a 1200 V, 30 A SiC SBD in a two-lead TO-220 package shown below.



1.1 Features

The following are key features of the MSC030SDA120K device:

- Zero recovery characteristics
- Low forward voltage
- Low leakage current
- Avalanche-energy rated
- RoHS compliant

1.2 Benefits

The following are benefits of the MSC030SDA120K device:

- High switching frequency
- Low switching losses
- Low noise (EMI) switching
- Higher reliability systems
- Increased system power density

1.3 Applications

The MSC030SDA120K device is designed for the following applications:

- Power factor correction (PFC)
- Anti-parallel diode
 - Switch-mode power supply
 - Inverters/converters
 - Motor controllers
- Freewheeling diode
 - Switch-mode power supply
 - Inverters/converters
- Snubber/clamp diode



2 Device Specifications

This section shows the specifications of the MSC030SDA120K device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the MSC030SDA120K device.

All ratings are taken at $T_c = 25$ °C unless otherwise specified.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter		Ratings	Unit
VR	Maximum DC reverse voltage		1200	V
VRRM	Maximum peak repetitive reverse voltage		_	
V _{RWM}	Maximum working peak reverse voltage		_	
l _F	Maximum DC forward current	Tc = 25 °C	70	Α
		Tc = 135 °C	32	=
		Tc = 145 °C	27	=
IFRM	Repetitive peak forward surge current (tp = 8.3 ms, half sine wave)		92	=
IFSM	Non-repetitive forward surge current (t _p = 8.3 ms, half sine wave)		165	=
Ртот	Power dissipation	Tc = 25 °C	300	W
		Tc = 110 °C	130	=
Tı , Tsтg	Operating junction and storage temperature range		–55 to 175	°C
Tι	Lead temperature for 10 seconds		300	=
Eas	Single pulse avalanche energy (starting T_1 = 25 °C, L = 0.22 mH, peak I_L = 30 A)		100	mJ

The following table shows the thermal and mechanical characteristics of the MSC030SDA120K device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Тур	Max	Unit
Rejc	Junction-to-case thermal resistance		0.35	0.50	°C/W
Wt	Package weight		0.07		OZ
			1.9		g
	Mounting torque, 6-32 or M3 screw			10	lbf-in
				1.1	N-m



2.2 Electrical Performance

The following table shows the static characteristics of the MSC030SDA120K device.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
VF	Forward Voltage	I _F = 30 A, T _J = 25 °C		1.5	1.8	V
		I _F = 30 A, T _J = 175 °C		2.1		≡
Irm	Reverse leakage current	V _R = 1200 V, T _J = 25 °C		9	200	μΑ
		V _R = 1200 V, T _J = 175 °C		150		-
Qc	Total capacitive charge	V _R = 600 V, T _J = 25 °C		130		nC
Cı	Junction capacitance	V _R = 400 V, T _J = 25 °C, f = 1 MHz		141		pF
	Junction capacitance	V _R = 800 V, T _J = 25 °C, f = 1 MHz		105		-



2.3

Typical Performance CurvesThis section shows the typical performance curves of the MSC030SDA120K device.

Figure 1 • Maximum Transient Thermal Impedance

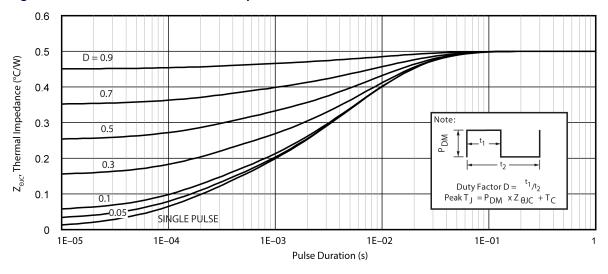


Figure 2 • Forward Current vs. Forward Voltage

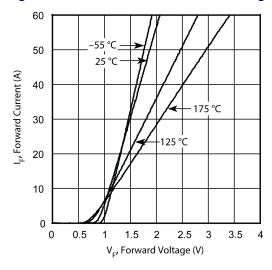


Figure 3 • Max. Forward Current vs. Case Temp.

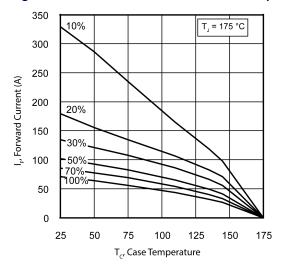




Figure 4 • Max. Power Dissipation vs. Case Temp.

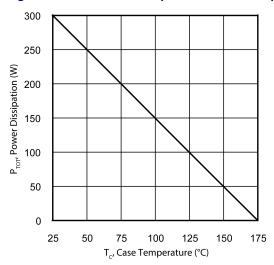


Figure 6 • Total Capacitive Charge vs. Reverse Voltage

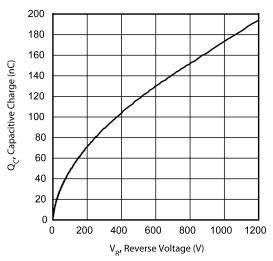


Figure 5 • Reverse Current vs. Reverse Voltage

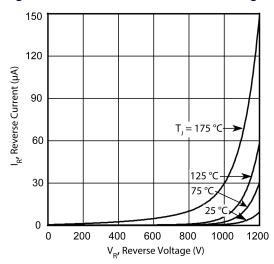
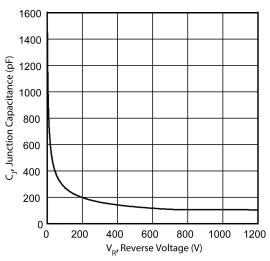


Figure 7 • Junction Capacitance vs. Reverse Voltage





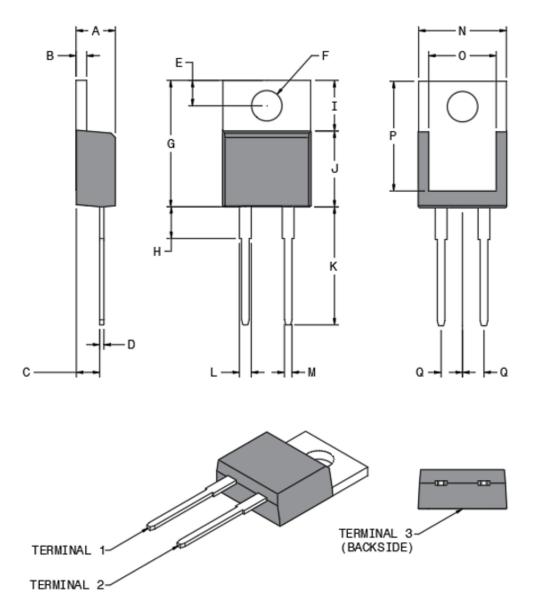
Package Specification 3

This section shows the package specification of the MSC030SDA120K device.

3.1

Package Outline Drawing
The following figure illustrates the TO-220 package drawing of the MSC030SDA120K device.

Figure 8 • Package Outline Drawing





The following table lists the TO-220 dimensions and should be used in conjunction with the package outline drawing.

Table 4 • TO-220 Dimensions

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)	
A	4.32	4.57	0.170	0.180	
В	1.14	1.40	0.045	0.055	
С	2.50	2.74	0.098	0.108	
D	0.36	0.53	0.014	0.021	
E	2.65	3.05	0.104	0.120	
F	3.60	3.96	0.142	0.156	
G	14.50	15.60	0.571	0.614	
Н	2.39	3.65	0.094	0.144	
I	6.00	6.80	0.236	0.268	
J	8.40	9.00	0.331	0.354	
К	13.00	14.00	0.512	0.551	
L	1.23	1.39	0.048	0.055	
М	0.69	0.88	0.027	0.035	
N	10.00	10.36	0.394	0.408	
0	7.57	7.90	0.298	0.311	
Р	12.20	13.10	0.480	0.516	
Q 2.54 BSC (nom.)		m.)	0.100 BSC (nom.)		
Terminal 1	Cathode				
Terminal 2	Anode				
Terminal 3	Cathode				





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